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ANDANTE

AI for New Devices And Technologies at the Edge

D2.7 Electrical evaluation of memory devices

Deliverable No.	D2.7	**Due Date**	*31-Aug-2020*
Type	Report	**Dissemination Level**	*Confidential*
Version	1.0	**Status**	Final
Description	Characterization results of memory devices: OxRAM, SOT-MRAM, FeFET and FeTFT, based on different parameters such as power consumption, speed, endurance, retention, and reliability		
Work Package	WP2 – New memory technologies for AI applications.		

Abstract (Published Summary)

D2.7 – Electrical evaluation of memory devices" within the ANDANTE project provides a comprehensive overview of the electrical characterization results for various memory types including RRAM, MRAM, FeFET, and FeTFT.

This deliverable offers valuable insights into the performance and behavior of these memory devices under different operating conditions. Through rigorous testing and analysis, the report sheds light on key parameters such as power consumption, endurance, retention, and switching speed, crucial for assessing their suitability for diverse applications.

With a focus on advancing memory technologies, this document serves as a significant resource for researchers and industry professionals aiming to optimize memory device performance and functionality in future electronic systems.